

# Detlef Hommel

## List of Publications by Year in descending order

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604  
papers

10,921  
citations

44069

48  
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56724

83  
g-index

607  
all docs

607  
docs citations

607  
times ranked

6848  
citing authors

#	ARTICLE	IF	CITATIONS
1	Superradiance of quantum dots. Nature Physics, 2007, 3, 106-110.	16.7	432
2	Fine Structure of Biexciton Emission in Symmetric and Asymmetric CdSe/ZnSe Single Quantum Dots. Physical Review Letters, 1999, 82, 1780-1783.	7.8	357
3	Microstructure of heteroepitaxial GaN revealed by x-ray diffraction. Journal of Applied Physics, 2003, 93, 8918-8925.	2.5	342
4	X-ray diffraction analysis of the defect structure in epitaxial GaN. Applied Physics Letters, 2000, 77, 2145-2147.	3.3	312
5	Free-carrier and phonon properties of n- and p-type hexagonal GaN films measured by infrared ellipsometry. Physical Review B, 2000, 62, 7365-7377.	3.2	233
6	Direct Observation of Optically Injected Spin-Polarized Currents in Semiconductors. Physical Review Letters, 2003, 90, 216601.	7.8	212
7	Emission properties of a-plane GaN grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2005, 98, 093519.	2.5	189
8	E0 band gap energy and lattice constant of ternary Zn <sub>1-x</sub> MgxSe as functions of composition. Applied Physics Letters, 1996, 69, 97-99.	3.3	188
9	The role of high-temperature island coalescence in the development of stresses in GaN films. Applied Physics Letters, 2001, 78, 1976-1978.	3.3	185
10	Biexciton versus Exciton Lifetime in a Single Semiconductor Quantum Dot. Physical Review Letters, 1999, 83, 4417-4420.	7.8	180
11	Single-photon emission of CdSe quantum dots at temperatures up to 200 K. Applied Physics Letters, 2002, 81, 2920-2922.	3.3	169
12	Composition mapping in InGaN by scanning transmission electron microscopy. Ultramicroscopy, 2011, 111, 1316-1327.	1.9	156
13	In situ and ex situ evaluation of the film coalescence for GaN growth on GaN nucleation layers. Journal of Crystal Growth, 2000, 221, 262-266.	1.5	137
14	Single zero-dimensional excitons in CdSe/ZnSe nanostructures. Applied Physics Letters, 1998, 73, 3105-3107.	3.3	134
15	Excitons, biexcitons, and phonons in ultrathin CdSe/ZnSe quantum structures. Physical Review B, 1999, 60, 8773-8782.	3.2	115
16	Direct observation of free-exciton thermalization in quantum-well structures. Physical Review B, 1998, 57, 1390-1393.	3.2	114
17	Strain relaxation in AlGaIn under tensile plane stress. Journal of Applied Physics, 2000, 88, 7029-7036.	2.5	113
18	Relaxation and mosaicity profiles in epitaxial layers studied by high resolution X-ray diffraction. Journal of Crystal Growth, 1994, 135, 41-52.	1.5	111

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19	Temperature dependence of the thermal expansion of GaN. Physical Review B, 2005, 72, .	3.2	105
20	Spectral diffusion of the exciton transition in a single self-organized quantum dot. Applied Physics Letters, 2000, 76, 1872-1874.	3.3	104
21	Stark effect and polarizability in a single CdSe/ZnSe quantum dot. Applied Physics Letters, 2001, 79, 1033-1035.	3.3	104
22	Anisotropic strain and phonon deformation potentials in GaN. Physical Review B, 2007, 75, .	3.2	99
23	Local vibrational modes in Mg-doped GaN grown by molecular beam epitaxy. Applied Physics Letters, 1999, 74, 3281-3283.	3.3	89
24	Quantum Optical Studies on Individual Acceptor Bound Excitons in a Semiconductor. Physical Review Letters, 2002, 89, 177403.	7.8	88
25	Incorporation of indium during molecular beam epitaxy of InGaN. Applied Physics Letters, 1998, 73, 3232-3234.	3.3	86
26	CdSe/ZnSe quantum structures grown by migration enhanced epitaxy: Structural and optical investigations. Applied Physics Letters, 1997, 71, 1510-1512.	3.3	83
27	Temperature dependence of the thermal expansion of AlN. Applied Physics Letters, 2009, 94, .	3.3	83
28	Binding-energy distribution and dephasing of localized biexcitons. Physical Review B, 1997, 55, R7383-R7386.	3.2	75
29	Stress and wafer bending of a-plane GaN layers on r-plane sapphire substrates. Journal of Applied Physics, 2006, 100, 103511.	2.5	67
30	Strong phase separation of strained In $\times$ Ga $\times$ alloys. Applied Physics Letters, 2006, 89, 103101.	3.2	66
31	Lateral quantization effects in lithographically defined CdZnSe/ZnSe quantum dots and quantum wires. Applied Physics Letters, 1995, 67, 124-126.	3.3	62
32	Density Dependence of the Exciton Energy in Semiconductors. Physical Review Letters, 1998, 80, 4943-4946.	7.8	62
33	Magnesium segregation and the formation of pyramidal defects in p-GaN. Applied Physics Letters, 2002, 81, 4748-4750.	3.3	62
34	Analysis of the Defect Structure of Epitaxial GaN. Physica Status Solidi A, 1999, 176, 391-395.	1.7	59
35	Suburban Transmission of Q Fever in French Guiana: Evidence of a Wild Reservoir. Journal of Infectious Diseases, 2001, 184, 278-284.	4.0	58
36	Room temperature single photon emission from an epitaxially grown quantum dot. Applied Physics Letters, 2012, 100, 061114.	3.3	58

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37	Plasmodium falciparum parasites in French Guiana: limited genetic diversity and high selfing rate.. American Journal of Tropical Medicine and Hygiene, 1999, 61, 978-985.	1.4	58
38	Optical and structural characterization of AlInN layers for optoelectronic applications. Journal of Applied Physics, 2010, 108, .	2.5	57
39	First order distributed feedback operation in ZnSe based laser structures. Applied Physics Letters, 1995, 67, 1-3.	3.3	56
40	CdSe/ZnSe Quantum Dot Structures: Structural and Optical Investigations. Physica Status Solidi (B): Basic Research, 1997, 202, 835-843.	1.5	53
41	Strain relaxation in AlGaN/GaN superlattices grown on GaN. Journal of Applied Physics, 2001, 89, 2160-2167.	2.5	53
42	Phase diagram and critical behavior of the random ferromagnet $Ga_{1-x}Mn_xN$ . Physical Review B, 2013, 88, .	3.2	53
43	Electron-phonon quantum kinetics in the strong-coupling regime. Physical Review B, 1999, 60, 12079-12090.	3.2	52
44	Electrically pumped lasing from CdSe quantum dots. Electronics Letters, 2001, 37, 1119.	1.0	51
45	Quantum dot formation by segregation enhanced CdSe reorganization. Journal of Applied Physics, 2002, 92, 6546-6552.	2.5	51
46	Intensity-dependent energy and line shape variation of donor-acceptor pair bands in ZnSe:N at different compensation levels. Applied Physics Letters, 1995, 67, 1914-1916.	3.3	49
47	Deep europium-bound exciton in a ZnS lattice. Physical Review B, 1990, 42, 3628-3633.	3.2	48
48	Dengue encephalitis in French Guiana. Research in Virology, 1998, 149, 235-238.	0.7	48
49	$Ga_{1-x}Mn_xN$ epitaxial films with high magnetization. Applied Physics Letters, 2012, 101, .	3.3	48
50	Mosaicity of GaN Epitaxial Layers: Simulation and Experiment. Physica Status Solidi (B): Basic Research, 2001, 228, 403-406.	1.5	44
51	560-nm-continuous wave laser emission from ZnSe-based laser diodes on GaAs. Applied Physics Letters, 2001, 79, 2523-2525.	3.3	44
52	Spatiotemporal dynamics of quantum-well excitons. Physical Review B, 2003, 67, .	3.2	43
53	Confined optical modes in monolithic II-VI pillar microcavities. Applied Physics Letters, 2006, 88, 051101.	3.3	43
54	Room temperature emission from $CdSe_{\hat{\cdot}}ZnSSe_{\hat{\cdot}}MgS$ single quantum dots. Applied Physics Letters, 2007, 90, 101114.	3.3	41

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55	Polarization-dependent formation of biexcitons in (Zn,Cd)Se/ZnSe quantum wells. <i>Physical Review B</i> , 1997, 55, 9866-9871.	3.2	39
56	In as a surfactant for the growth of GaN (0001) by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001, 79, 3425-3427.	3.3	39
57	500-560 nm Laser Emission from Quaternary CdZnSse Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 935-942.	1.5	39
58	Single photon emission from InGaN/GaN quantum dots up to 50â€%K. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	39
59	Determination of the Temperature Dependent Thermal Expansion Coefficients of Bulk AlN by HRXRD. <i>Acta Physica Polonica A</i> , 2008, 114, 1193-1200.	0.5	38
60	Formation of self-assembling IIâ€VI semiconductor nanostructures during migration enhanced epitaxy. <i>Journal of Crystal Growth</i> , 1998, 184-185, 259-263.	1.5	37
61	Energy structure and recombination for ZnS bulk crystals doped with Tb, Er and Eu. <i>Journal of Crystal Growth</i> , 1985, 72, 346-350.	1.5	36
62	Impact of defects on the carrier transport in GaN. <i>Journal of Crystal Growth</i> , 1998, 189-190, 763-767.	1.5	36
63	Segregation-enhanced etching of Cd during Zn deposition on CdSe quantum dots. <i>Physical Review B</i> , 2001, 64, .	3.2	36
64	Eu <sup>2+</sup> photocharge transfer processes in zns crystals determined by photo-esr measurements. <i>Physica Status Solidi A</i> , 1986, 95, 261-268.	1.7	35
65	Propagation of femtosecond pulses in thin ZnSe layers. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 196, 473-485.	1.5	35
66	Structural defect-related emissions in nonpolar a-plane GaN. <i>Physica B: Condensed Matter</i> , 2006, 376-377, 473-476.	2.7	34
67	Influence of Coulomb correlations on gain and stimulated emission in (Zn,Cd)Se/Zn(S,Se)/(Zn,Mg)(S,Se) quantum-well lasers. <i>Physical Review B</i> , 1998, 58, 2055-2063.	3.2	33
68	New Concept for ZnTe-Based Homoepitaxial Light-Emitting Diodes Grown by Molecular Beam Epitaxy. <i>Physica Status Solidi A</i> , 2002, 192, 177-182.	1.7	33
69	Polarization dynamics in self-assembled CdSe/ZnSe quantum dots:â€fThe role of excess energy. <i>Physical Review B</i> , 2003, 67, .	3.2	33
70	Green monolithic IIâ€VI vertical-cavity surface-emitting laser operating at room temperature. <i>Physica Status Solidi (B): Basic Research</i> , 2004, 241, 731-738.	1.5	32
71	High-reflectivity broadband distributed Bragg reflector lattice matched to ZnTe. <i>Applied Physics Letters</i> , 2009, 94, 191108.	3.3	32
72	Blueâ€Green ZnSe Laser Diodes for Optoelectronics. Present State at WÃ¼rzburg University. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 269-277.	1.5	31

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73	High-density effects, stimulated emission, and electrooptical properties of ZnCdSe/ZnSe single quantum wells and laser diodes. <i>Physica Status Solidi (B): Basic Research</i> , 1996, 194, 199-217.	1.5	31
74	Dynamical properties of excitons in Zn <sub>1-x</sub> CdxSe/ZnSe quantum wells and Zn <sub>1-x</sub> CdxSe epilayers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1994, 138, 861-867.	1.5	30
75	Optical properties of Zn <sub>1-x</sub> MgxSySe <sub>1-y</sub> epitaxial layers for blue-green laser applications. <i>Journal of Applied Physics</i> , 1995, 77, 5377-5380.	2.5	30
76	Ion-induced crystal damage during plasma-assisted MBE growth of GaN layers. <i>Physical Review B</i> , 1998, 58, 15749-15755.	3.2	30
77	Thermal expansion of bulk and homoepitaxial GaN. <i>Applied Physics Letters</i> , 2000, 77, 1434-1436.	3.3	30
78	Strain in cracked AlGaIn layers. <i>Journal of Applied Physics</i> , 2002, 92, 118-123.	2.5	30
79	InGaIn quantum dot growth in the limits of Stranski-Krastanov and spinodal decomposition. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1765-1776.	1.5	30
80	Inhibition and Enhancement of the Spontaneous Emission of Quantum Dots in Micropillar Cavities with Radial-Distributed Bragg Reflectors. <i>ACS Nano</i> , 2014, 8, 9970-9978.	14.6	30
81	First Case of Yellow Fever in French Guiana since 1902. <i>Emerging Infectious Diseases</i> , 1999, 5, 429-432.	4.3	29
82	Acute Renal Failure Associated with Dengue Fever in French Guiana. <i>Nephron</i> , 1999, 83, 183-183.	1.8	29
83	Single-electron charging of a self-assembled InAs quantum dot. <i>Applied Physics Letters</i> , 2003, 82, 3946-3948.	3.3	29
84	Optical bandpass switching by modulating a microcavity using ultrafast acoustics. <i>Physical Review B</i> , 2010, 81, .	3.2	29
85	Analysis of deep traps in hexagonal molecular beam epitaxy-grown GaN by admittance spectroscopy. <i>Journal of Applied Physics</i> , 1998, 84, 2040-2043.	2.5	28
86	Preconditioning of c-plane sapphire for GaN molecular beam epitaxy by electron cyclotron resonance plasma nitridation. <i>Journal of Applied Physics</i> , 1998, 83, 6023-6027.	2.5	28
87	Multiple African Honeybee Stings and Acute Renal Failure. <i>Nephron</i> , 1998, 78, 235-236.	1.8	27
88	Negatively charged trion in ZnSe single quantum wells with very low electron densities. <i>Physical Review B</i> , 2000, 62, 7413-7419.	3.2	27
89	Micro-photoluminescence studies of InGaIn/GaN quantum dots up to 150 K. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1661-1664.	1.5	27
90	Observation of a hybrid state of Tamm plasmons and microcavity exciton polaritons. <i>Scientific Reports</i> , 2016, 6, 34392.	3.3	27

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91	Bandgap engineering in III-nitrides with boron and group V elements: Toward applications in ultraviolet emitters. Applied Physics Reviews, 2020, 7, .	11.3	27
92	Optically detected cyclotron resonance properties of high purity ZnSe epitaxial layers grown on GaAs. Applied Physics Letters, 1997, 71, 1116-1117.	3.3	26
93	Highly ordered catalyst-free and mask-free GaN nanorods on-plane sapphire. Nanotechnology, 2009, 20, 075604.	2.6	26
94	Band gap bowing of binary alloys: Experimental results compared to theoretical tight-binding supercell calculations for $\langle \text{Cd} \rangle$ . Physical Review B, 2010, 82, .	3.2	26
95	Fabrication of CdZnSe/ZnSe quantum dots and quantum wires by electron beam lithography and wet chemical etching. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2792.	1.6	25
96	Laterally structured ZnCdSe/ZnSe superlattices by diffusion induced disordering. Applied Physics Letters, 1996, 69, 2647-2649.	3.3	25
97	Raman scattering from defects in GaN: The question of vibrational or electronic scattering mechanism. Physical Review B, 1998, 58, 13619-13626.	3.2	25
98	Size dependence of strain relaxation and lateral quantization in deep etched $\text{Cd}_{x}\text{Zn}_{1-x}\text{Se}/\text{ZnSe}$ quantum wires. Physical Review B, 1998, 57, 15439-15447.	3.2	25
99	Near-field photoluminescence imaging of single defects in a ZnSe quantum-well structure at low temperatures. Applied Physics Letters, 2000, 76, 203-205.	3.3	25
100	Polariton propagation in shallow-confinement heterostructures: Microscopic theory and experiment showing the breakdown of the dead-layer concept. Physical Review B, 2004, 70, .	3.2	25
101	Electroluminescence from a single InGaN quantum dot in the green spectral region up to 150 K. Nanotechnology, 2010, 21, 015204.	2.6	25
102	Exciton-Polariton Gas as a Nonequilibrium Coolant. Physical Review Letters, 2015, 114, 186403.	7.8	25
103	Nature of the charge transfer states of the trigonal and tetragonal $\text{Eu}^{3+}$ centers in $\text{CdF}_2$ crystals. Journal of Luminescence, 1979, 18-19, 281-284.	3.1	24
104	p-type Doping of ZnSe. On the Properties of Nitrogen in ZnSe:N. Physica Status Solidi (B): Basic Research, 1995, 187, 393-399.	1.5	24
105	Electro-Optical Characterization of CdSe Quantum Dot Laser Diodes. Physica Status Solidi (B): Basic Research, 2002, 229, 1029-1032.	1.5	24
106	XPS studies on the role of arsenic incorporated into GaN. Vacuum, 2019, 167, 73-76.	3.5	24
107	Two-dimensional Shubnikov-de Haas oscillations in modulation-doped CdTe/CdMnTe quantum well structures. Applied Physics Letters, 1993, 62, 3010-3012.	3.3	23
108	The growth start on the heterovalent GaAs-ZnSe interface under Te, Se and Zn termination. Journal of Crystal Growth, 1996, 159, 761-765.	1.5	23

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109	Molecular beam epitaxial growth and characterization of ZnSe on (001) ZnSe substrates and its application in light-emitting diodes. <i>Semiconductor Science and Technology</i> , 1996, 11, 107-115.	2.0	23
110	Doping dependent ZnCdSe/ZnSe-superlattice disordering. <i>Applied Physics Letters</i> , 1997, 71, 243-245.	3.3	23
111	Exciton localisation in CdSe islands buried in a quantum well of Zn <sub>1-x</sub> Cd <sub>x</sub> Se. <i>Journal of Crystal Growth</i> , 1998, 184-185, 306-310.	1.5	23
112	Compensation mechanisms in ZnSe:N and codoped ZnSe:N:Cl. <i>Physical Review B</i> , 1998, 57, 12869-12873.	3.2	23
113	Compensation mechanism in MOCVD and MBE grown GaN:Mg. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 38-41.	2.7	23
114	Green laser emission from monolithic II-VI-based pillar microcavities near room temperature. <i>Applied Physics Letters</i> , 2008, 92, 031101.	3.3	23
115	Strong coupling in monolithic microcavities with ZnSe quantum wells. <i>Applied Physics Letters</i> , 2012, 100, 161104.	3.3	23
116	Micropillar Cavity Containing a CdTe Quantum Dot with a Single Manganese Ion. <i>Crystal Growth and Design</i> , 2014, 14, 988-992.	3.0	23
117	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. <i>Scientific Reports</i> , 2017, 7, 41877.	3.3	23
118	Radiative recombination centers induced by stacking-fault pairs in ZnSe/ZnMgSSe quantum-well structures. <i>Applied Physics Letters</i> , 1999, 75, 3944-3946.	3.3	22
119	Spatially modified layer properties related to the formation of gallium droplets on GaN(0001) surfaces during plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001, 78, 3827-3829.	3.3	22
120	Stress analysis of Al <sub>x</sub> Ga <sub>1-x</sub> N films with microcracks. <i>Applied Physics Letters</i> , 2003, 82, 367-369.	3.3	22
121	Enhanced spontaneous emission of CdSe quantum dots in monolithic II-VI pillar microcavities. <i>Applied Physics Letters</i> , 2006, 89, 091107.	3.3	22
122	Optical Study of ZnS:Mn Thin Films with High Mn Concentrations. <i>Physica Status Solidi A</i> , 1984, 81, 695-700.	1.7	21
123	Chlorine: A new efficient $\delta$ -type dopant in CdTe layers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1992, 61, 1546-1548.	3.3	21
124	Measurements of the absolute external luminescence quantum efficiency in ZnSe/ZnMgSSe multiple quantum wells as a function of temperature. <i>Journal of Applied Physics</i> , 1998, 84, 6871-6876.	2.5	21
125	Device Properties of Homo- and Heteroepitaxial ZnSe-Based Laser Diodes. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2590-2597.	1.5	21
126	Realization of a GaN Laser Diode with Wet Etched Facets. <i>Physica Status Solidi A</i> , 2002, 191, R3-R5.	1.7	21



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127	Heat generation and dissipation in GaN-based light emitting devices. <i>Physica Status Solidi A</i> , 2003, 200, 83-86.	1.7	21
128	Pronounced Purcell enhancement of spontaneous emission in CdTe/ZnTe quantum dots embedded in micropillar cavities. <i>Applied Physics Letters</i> , 2012, 101, 132105.	3.3	21
129	Optical study of interdiffusion in CdTe and ZnSe based quantum wells. <i>Journal of Crystal Growth</i> , 1994, 138, 362-366.	1.5	20
130	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. <i>Journal of Electronic Materials</i> , 2004, 33, 389-394.	2.2	20
131	Resonant modes in monolithic nitride pillar microcavities. <i>European Physical Journal B</i> , 2005, 48, 291-294.	1.5	20
132	Spatially resolved distribution of dislocations and crystallographic tilts in GaN layers grown on Si(111) substrates by maskless cantilever epitaxy. <i>Journal of Applied Physics</i> , 2006, 100, 053103.	2.5	20
133	The dominant shallow 0.225 eV acceptor in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1604-1608.	1.5	20
134	Electrically driven single quantum dot emitter operating at room temperature. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	20
135	Growth and characterization of nitride-based distributed Bragg reflectors. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1748-1755.	1.5	20
136	Determination of dislocation density in GaN/sapphire layers using XRD measurements carried out from the edge of the sample. <i>Journal of Alloys and Compounds</i> , 2020, 825, 153838.	5.5	20
137	Direct observation of localized impurity excited states degenerate with conduction band (CdF <sub>2</sub> : Eu). <i>Journal of Luminescence</i> , 1981, 24-25, 217-220.	3.1	19
138	Molecular beam epitaxial growth mechanism of ZnSe epilayers on (100) GaAs as determined by reflection high-energy electron diffraction, transmission electron microscopy and X-ray diffraction. <i>Journal of Crystal Growth</i> , 1994, 138, 48-54.	1.5	19
139	Intensity-dependent energy and lineshape variation of donor-acceptor-pair bands in highly compensated ZnSe:N. <i>Journal of Crystal Growth</i> , 1996, 159, 252-256.	1.5	19
140	Plasma assisted molecular beam epitaxy growth of GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997, 50, 12-15.	3.5	19
141	Thermalization of free excitons in ZnSe quantum wells. <i>Journal of Crystal Growth</i> , 1998, 184-185, 795-800.	1.5	19
142	Thermally induced stress in GaN layers with regard to film coalescence. <i>Journal of Crystal Growth</i> , 2001, 230, 357-360.	1.5	19
143	X-ray scattering from GaN epitaxial layers - an example of highly anisotropic coherence. <i>Journal Physics D: Applied Physics</i> , 2001, 34, A25-A29.	2.8	19
144	Fine tuning of quantum-dot pillar microcavities by focused ion beam milling. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	19

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145	Q Fever in French Guiana: New Trends. <i>Emerging Infectious Diseases</i> , 1998, 4, 131-132.	4.3	19
146	Recombination processes in ZnS:Sm. <i>Physical Review B</i> , 1991, 43, 9955-9958.	3.2	18
147	Bleaching of excitons in a (Zn,Cd)Se/Zn(S,Se)/(Zn,Mg)(S,Se) laser diode under lasing conditions. <i>Physical Review B</i> , 1995, 52, 4736-4739.	3.2	18
148	High-resolution x-ray diffraction investigations of highly mismatched II-VI quantum wells. <i>Journal Physics D: Applied Physics</i> , 1999, 32, A42-A46.	2.8	18
149	Growth of self-assembled (Zn)CdSe nanostructures on ZnSe by migration enhanced epitaxy. <i>Journal of Crystal Growth</i> , 1999, 201-202, 1222-1225.	1.5	18
150	Internal photoluminescence in ZnSe homoepitaxy and application in blue-green-orange mixed-color light-emitting diodes. <i>Journal of Crystal Growth</i> , 2000, 214-215, 1075-1079.	1.5	18
151	Manipulating single quantum dot states in a lateral electric field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 147-150.	2.7	18
152	Bound polarons in semiconductor nanostructures. <i>Physical Review B</i> , 2003, 67, .	3.2	18
153	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. <i>Journal of Alloys and Compounds</i> , 2018, 747, 946-959.	5.5	18
154	Thermoluminescence and photochromism of CdF <sub>2</sub> : Eu. <i>Physica Status Solidi A</i> , 1975, 31, K81-K84.	1.7	17
155	Bromine doping of CdTe and CdMnTe epitaxial layers grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1993, 129, 243-248.	1.5	17
156	The growth of HgSe by molecular beam epitaxy for ohmic contacts to p-ZnSe. <i>Journal of Crystal Growth</i> , 1994, 138, 471-476.	1.5	17
157	Exciton Dynamics and Gain Mechanisms in Optically Pumped ZnSe-Based Laser Structures. <i>Physica Status Solidi (B): Basic Research</i> , 1995, 187, 423-434.	1.5	17
158	Biexciton formation in CdxZn1-xSe/ZnSe quantum-dot and quantum-well structures. <i>Physical Review B</i> , 1997, 56, 15261-15263.	3.2	17
159	Biexcitonic gain characteristics in ZnSe-based lasers with binary wells. <i>Physical Review B</i> , 1999, 60, 5743-5750.	3.2	17
160	Compositional inhomogeneities in InGaN studied by transmission electron microscopy and spatially resolved cathodoluminescence. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999, 59, 279-282.	3.5	17
161	Nondestructive detection of stacking faults for optimization of CdSe/ZnSe quantum-dot structures. <i>Applied Physics Letters</i> , 2000, 77, 3544-3546.	3.3	17
162	Optical Gain of CdSe Quantum Dot Stacks. <i>Physica Status Solidi A</i> , 2002, 190, 593-597.	1.7	17

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163	ZnSe-based laser diodes: New approaches. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1098-1105.	0.8	17
164	First order gain and index coupled distributed feedback lasers in ZnSe-based structures with finely tunable emission wavelengths. <i>Applied Physics Letters</i> , 1996, 68, 599-601.	3.3	16
165	Spin-flip Raman scattering of wide-band-gap II-VI ternary alloys. <i>Physical Review B</i> , 1999, 60, 13555-13560.	3.2	16
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167	Optical and Structural Properties of CdSe/Zn(S)Se Quantum Dot Stacks. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 224, 143-146.	1.5	16
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